

# PolarHV™ HiPerFET Power MOSFET

**IXFH 24N80P**  
**IXFK 24N80P**  
**IXFT 24N80P**

$V_{DSS} = 800 \text{ V}$   
 $I_{D25} = 24 \text{ A}$   
 $R_{DS(on)} \leq 400 \text{ m}\Omega$   
 $t_{rr} \leq 250 \text{ ns}$

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode



Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	800	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1 \text{ M}\Omega$	800	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	24	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	55	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	12	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	50	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	1.5	J
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 2 \Omega$	10	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	650	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$M_d$	Mounting torque (TO-247 & TO-264)	1.13/10 Nm/lb.in.	
Weight	TO-247	6	g
	TO-268	5	g
	TO-264	10	g
$T_L$	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic body for 10 s	260	$^\circ\text{C}$

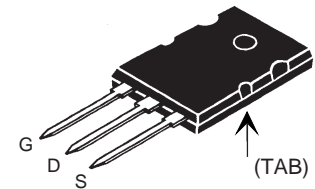
TO-247 (IXFH)



TO-268 (IXFT) Case Style



TO-264 AA (IXFK)



G = Gate    D = Drain  
S = Source    Tab = Drain

## Features

- International standard packages
- Fast recovery diode
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect

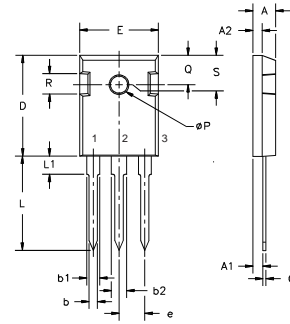
## Advantages

- Easy to mount
- Space savings
- High power density

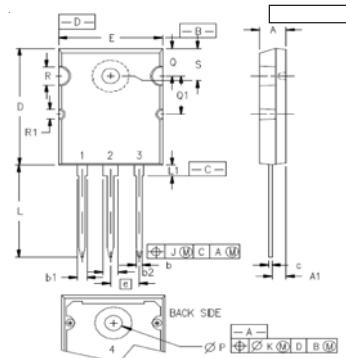
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	800		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4 \text{ mA}$	3.0		5.0 V
$I_{GSS}$	$V_{GS} = \pm 30 \text{ V}$ , $V_{DS} = 0 \text{ V}$			$\pm 100 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$			25 $\mu\text{A}$
	$V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			1000 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $d \leq 2\%$			400 $\text{m}\Omega$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{ V}; I_D = 0.5 I_{D25}$ pulse test	15	25	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		7200	pF
$C_{oss}$			470	pF
$C_{rss}$			26	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 I_{D25}$ $R_G = 2\ \Omega$ (External)		32	ns
$t_r$			27	ns
$t_{d(off)}$			75	ns
$t_f$			24	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$		105	nC
$Q_{gs}$			30	nC
$Q_{gd}$			33	nC
$R_{thJC}$			0.19	$^\circ\text{C/W}$
$R_{thCS}$	TO-247		0.21	$^\circ\text{C/W}$
$R_{thCS}$	TO-264		0.15	$^\circ\text{C/W}$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{ V}$			24 A
$I_{SM}$	Repetitive			55 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$			250 ns
$Q_{RM}$			0.8	$\mu\text{C}$
$I_{RM}$			6.0	A

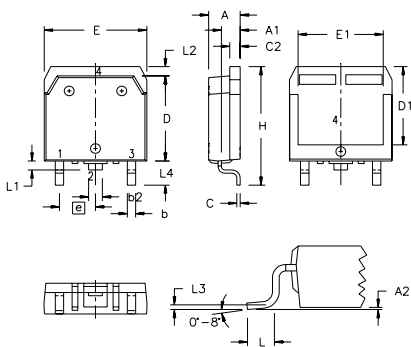
**TO-247 AD (IXFH) Outline**


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

**TO-264 (IXFK) Outline**


- 1 - GATE  
2, 4 - DRAIN (COLLECTOR)  
3 - SOURCE (EMITTER)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A <sub>1</sub>	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b <sub>1</sub>	.087	.102	2.21	2.59
b <sub>2</sub>	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L <sub>1</sub>	.087	.102	2.21	2.59
∅P	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q <sub>1</sub>	.330	.346	8.38	8.79
∅R	.155	.187	3.94	4.75
∅R <sub>1</sub>	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

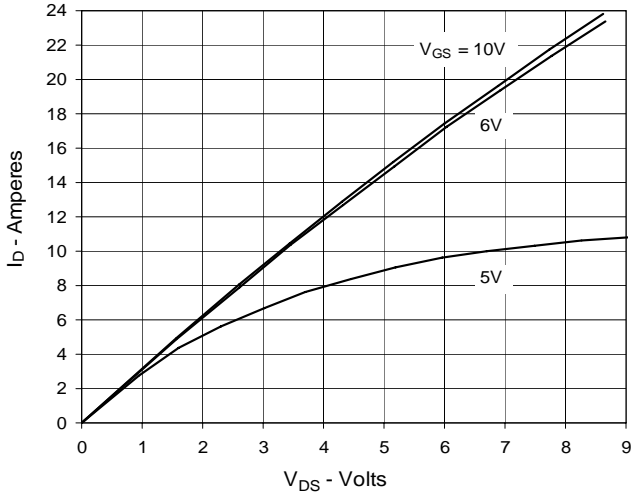
**TO-268 (IXFT) Outline**


SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A <sub>1</sub>	.106	.114	2.70	2.90
A <sub>2</sub>	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b <sub>2</sub>	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C <sub>2</sub>	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D <sub>1</sub>	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E <sub>1</sub>	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L <sub>1</sub>	.047	.055	1.20	1.40
L <sub>2</sub>	.039	.045	1.00	1.15
L <sub>3</sub>	.010 BSC		0.25 BSC	
L <sub>4</sub>	.150	.161	3.80	4.10

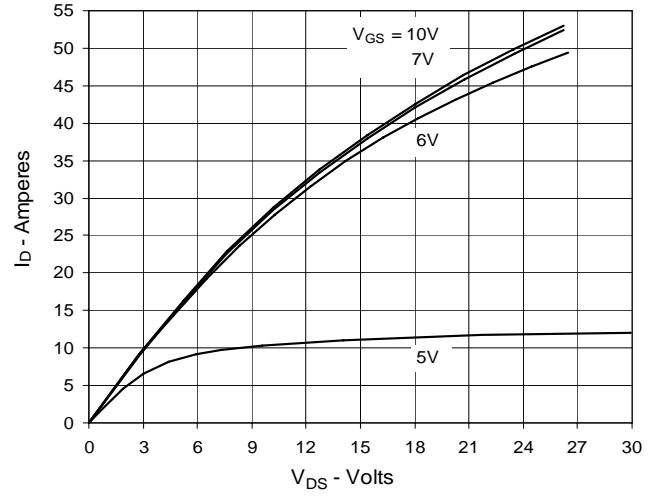
IXYS reserves the right to change limits, test conditions, and dimensions.

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one or more of the following U.S. patents: 4,850,072 5,017,508 5,063,307 5,381,025 6,259,123 B1 6,534,343 6,710,405 B2 6,759,692  
4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2

**Fig. 1. Output Characteristics @ 25°C**



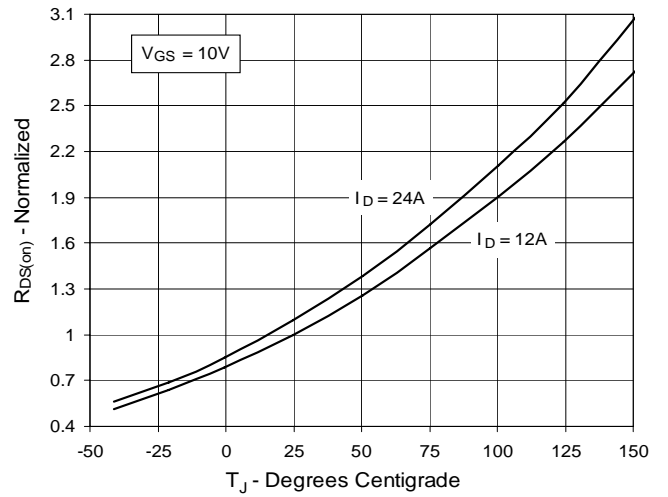
**Fig. 2. Extended Output Characteristics @ 25°C**



**Fig. 3. Output Characteristics @ 125°C**



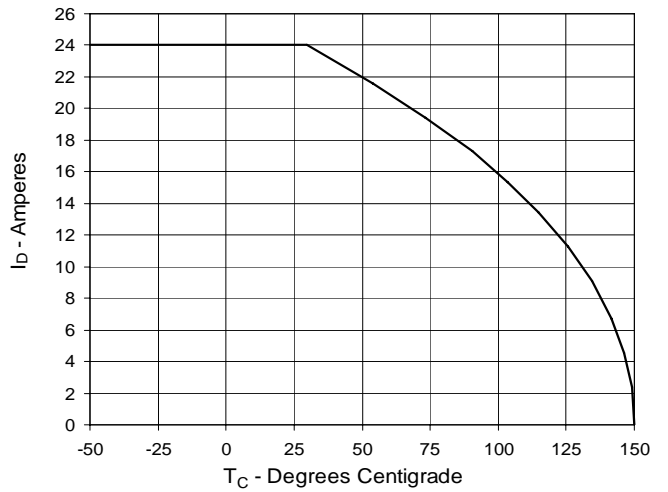
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 12A$  Value vs. Junction Temperature**



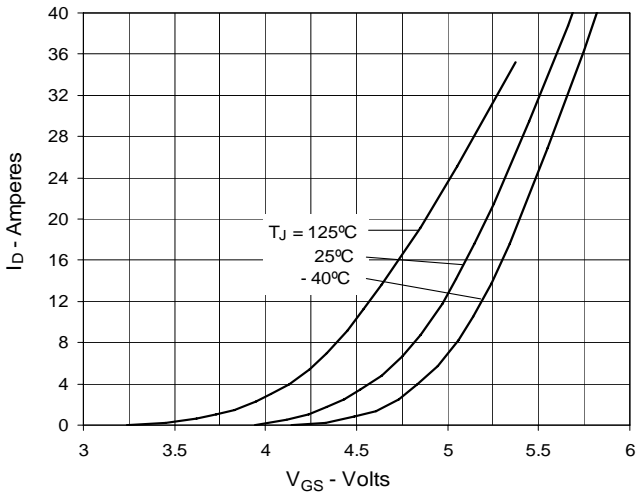
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 12A$  Value vs. Drain Current**



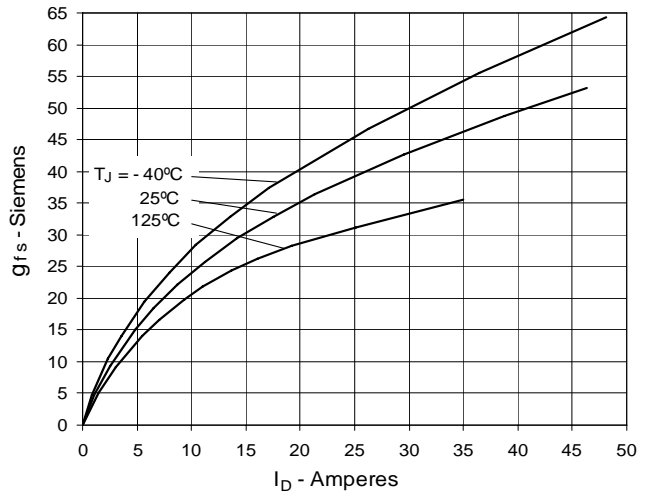
**Fig. 6. Maximum Drain Current vs. Case Temperature**



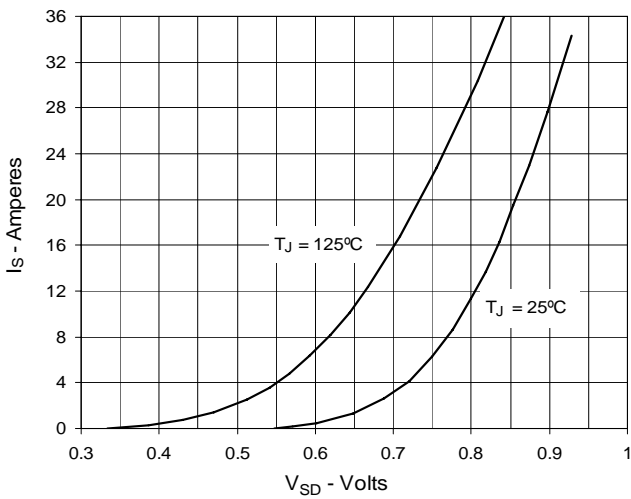
**Fig. 7. Input Admittance**



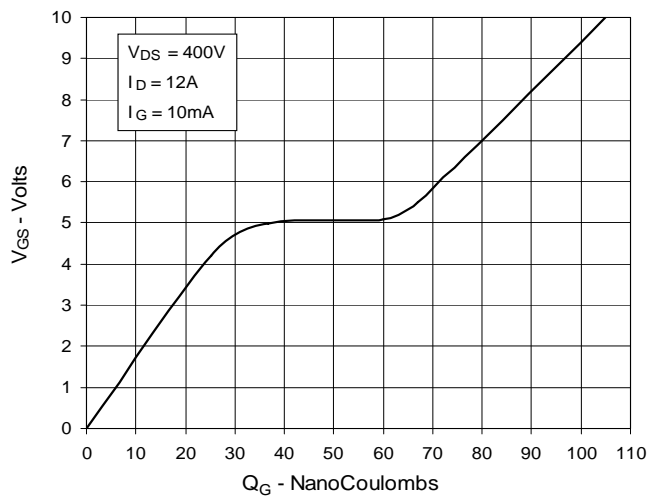
**Fig. 8. Transconductance**



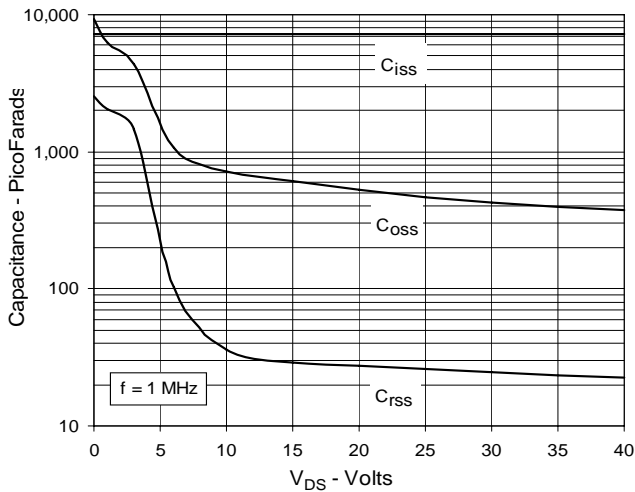
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



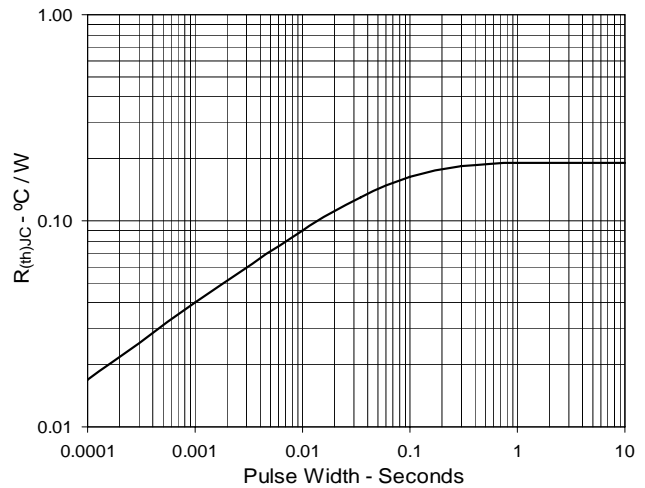
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Resistance**





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